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3.22 Mechanical Properties of Materials  
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**Group: Effects of multidimensional defects on III-V semiconductor mechanics**  
PS2 part b work detailing calculations of Young's modulus

We use the following equation to solve for Young's modulus in the different directions:

$$\frac{1}{E_{[hkl]}} = S_{11} - 2[(S_{11} - S_{12}) - \frac{1}{2}S_{44}][\alpha^2\beta^2 + \alpha^2\gamma^2 + \beta^2\gamma^2]$$

From the review article we see that

$$E_{\langle 100 \rangle} = \frac{1}{S_{11}} = 8.547 \times 10^{10} \text{ Pa}$$

and using  $\alpha = \beta = \gamma = \frac{1}{\sqrt{3}}$

$$E_{\langle 111 \rangle} = 1.422 \times 10^{11} \text{ Pa}$$

for  $\alpha = \beta = \frac{1}{\sqrt{2}}$  in the  $\langle 110 \rangle$  direction

$$E_{\langle 110 \rangle} = 1.22 \times 10^{11} \text{ Pa}$$

We conclude that the  $\langle 111 \rangle$  direction is the direction with the highest Young's modulus, hence it will be more resistant to stretching in the direction.